

Åemsettin Altindal

List of Publications by Year in descending order

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143
papers

3,963
citations

109321

35
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182427

51
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144
all docs

144
docs citations

144
times ranked

1477
citing authors

#	ARTICLE	IF	CITATIONS
1	Dielectric properties, electric modulus and conductivity profiles of Al/Al ₂ O ₃ /p-Si type MOS capacitor in large frequency and bias interval. Engineering Science and Technology, an International Journal, 2022, 27, 101017.	3.2	10
2	Dielectric Properties of PVP: BaTiO ₃ Interlayer in the Al/PVP: BaTiO ₃ /P-Si Structure. Silicon, 2022, 14, 5437-5443.	3.3	12
3	High Dielectric Performance of Heterojunction Structures Based on Spin-Coated Graphene-PVP Thin Film on Silicon With Gold Contacts for Organic Electronics. IEEE Transactions on Electron Devices, 2022, 69, 304-310.	3.0	10
4	Identification of Current Transport Mechanisms and Temperature Sensing Qualifications for Al/(ZnS-PVA)/p-Si Structures at Low and Moderate Temperatures. IEEE Sensors Journal, 2022, 22, 99-106.	4.7	18
5	A comparison of Au/n-Si Schottky diodes (SDs) with/without a nanographite (NG) interfacial layer by considering interlayer, surface states (N _{ss}) and series resistance (R _s) effects. Physica Scripta, 2022, 97, 055811.	2.5	17
6	The illumination effects on the current conduction mechanisms of the Au/(Er ₂ O ₃ :PVC)/Si (MPS) Schottky diodes. Journal of Applied Polymer Science, 2022, 139, .	2.6	19
7	Discrepancies in barrier heights obtained from current-voltage (IV) and capacitance-voltage (CV) of Au/PNO-MPhPPy/n-GaAs structures in wide range of temperature. Journal of Materials Science: Materials in Electronics, 2022, 33, 12210-12223.	2.2	17
8	Dielectric properties and negative-capacitance/dielectric in Au/n-Si structures with PVC and (PVC:Sm ₂ O ₃) interlayer. Materials Science in Semiconductor Processing, 2022, 147, 106754.	4.0	13
9	The effect of cadmium impurities in the (PVP-TeO ₂) interlayer in Al/p-Si (MS) Schottky barrier diodes (SBDs): Exploring its electrophysical parameters. Physica B: Condensed Matter, 2021, 604, 412617.	2.7	18
10	Current transport properties of (Au/Ni)/HfAlO ₃ /n-Si metal-insulator-semiconductor junction. Journal of Physics and Chemistry of Solids, 2021, 148, 109758.	4.0	23
11	Frequency Response of C _v and G/f _o -V Characteristics of Au/(Nanographite-doped PVP)/n-Si Structures. Journal of Materials Science: Materials in Electronics, 2021, 32, 993-1006.	2.2	20
12	Investigation of the variation of dielectric properties by applying frequency and voltage to Al/(CdS-PVA)/p-Si structures. Journal of Molecular Structure, 2021, 1224, 129325.	3.6	24
13	Electrical characterization of Au/n-Si (MS) diode with and without graphene-polyvinylpyrrolidone (Gr-PVP) interface layer. Journal of Materials Science: Materials in Electronics, 2021, 32, 3451-3459.	2.2	19
14	Frequency dependence of the dielectric properties of Au/(NG:PVP)/n-Si structures. Journal of Materials Science: Materials in Electronics, 2021, 32, 7657-7670.	2.2	25
15	Evaluation of gamma-irradiation effects on the electrical properties of Al/(ZnO-PVA)/p-Si type Schottky diodes using current-voltage measurements. Radiation Physics and Chemistry, 2021, 183, 109430.	2.8	29
16	Illumination and voltage effects on the forward and reverse bias current-voltage (I-V) characteristics in In/In ₂ S ₃ /p-Si photodiodes. Journal of Materials Science: Materials in Electronics, 2021, 32, 21825-21836.	2.2	21
17	Effect of (Co-TeO ₂ -doped polyvinylpyrrolidone) organic interlayer on the electrophysical characteristics of Al/p-Si (MS) structures. Journal of Materials Science: Materials in Electronics, 2021, 32, 21909-21922.	2.2	16
18	A comparison of electrical characteristics of Au/n-Si (MS) structures with PVC and (PVC: Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50.62 Td (S	2.5	35

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19	Graphene doped (Bi ₂ Te ₃ Bi ₂ O ₃ TeO ₂): PVP dielectrics in metal-semiconductor structures. Applied Physics A: Materials Science and Processing, 2021, 127, 1.	2.3	11
20	Comparison of dielectric characteristics for metal-semiconductor structures fabricated with different interlayers thicknesses. Journal of Materials Science: Materials in Electronics, 2021, 32, 26700-26708.	2.2	3
21	Frequency Response of Metal-Semiconductor Structures With Thin-Films Sapphire Interlayer by ALD Technique. IEEE Transactions on Electron Devices, 2021, 68, 5085-5089.	3.0	11
22	Comparison of the electrical and impedance properties of Au/(ZnOMn:PVP)/n-Si (MPS) type Schottky-diodes (SDs) before and after gamma-irradiation. Physica Scripta, 2021, 96, 125881.	2.5	20
23	Comparison of electrical properties of MS and MPS type diode in respect of (In ₂ O ₃ -PVP) interlayer. Physica B: Condensed Matter, 2020, 576, 411733.	2.7	46
24	Frequency and voltage dependence of barrier height, surface states, and series resistance in Al/Al ₂ O ₃ /p-Si structures in wide range frequency and voltage. Physica B: Condensed Matter, 2020, 582, 411979.	2.7	51
25	Effect of illumination on electrical parameters of Au/(P3DMTFT)/n-GaAs Schottky barrier diodes. Indian Journal of Physics, 2020, 94, 1901-1908.	1.8	25
26	Identifying of series resistance and interface states on rhenium/n-GaAs structures using C-V and G/ω-V characteristics in frequency ranged 50 kHz to 5 MHz. Journal of Materials Science: Materials in Electronics, 2020, 31, 704-713.	2.2	5
27	The effects of (Bi ₂ Te ₃ Bi ₂ O ₃ -TeO ₂ -PVP) interfacial film on the dielectric and electrical features of Al/p-Si (MS) Schottky barrier diodes (SBDs). Physica B: Condensed Matter, 2020, 582, 411958.	2.7	33
28	Electrical and dielectric properties of Al/(PVP: Zn-TeO ₂)/p-Si heterojunction structures using current-voltage (I-V) and impedance-frequency (Z-f) measurements. Applied Physics A: Materials Science and Processing, 2020, 126, 1.	2.3	33
29	Electrical characteristics of Au/PVP/n-Si structures using admittance measurements between 1 and 500 kHz. Journal of Materials Science: Materials in Electronics, 2020, 31, 13337-13343.	2.2	7
30	Electric and dielectric parameters in Au/n-Si (MS) capacitors with metal oxide-polymer interlayer as function of frequency and voltage. Journal of Materials Science: Materials in Electronics, 2020, 31, 15589-15598.	2.2	26
31	Investigation of effects on dielectric properties of different doping concentrations of Au/Gr-PVA/p-Si structures at 0.1 and 1 MHz at room temperature. Journal of Materials Science: Materials in Electronics, 2020, 31, 16324-16331.	2.2	3
32	A comparison study regarding Al/p-Si and Al/(carbon nanofiber-PVP)/p-Si diodes: current/impedance-voltage (I/Z-V) characteristics. Applied Physics A: Materials Science and Processing, 2020, 126, 1.	2.3	13
33	A Highly Sensitive Temperature Sensor Based on Au/Graphene-PVP/n-Si Type Schottky Diodes and the Possible Conduction Mechanisms in the Wide Range Temperatures. IEEE Sensors Journal, 2020, 20, 14081-14089.	4.7	37
34	A comparative study on the electrical properties and conduction mechanisms of Au/n-Si Schottky diodes with/without an organic interlayer. Journal of Materials Science: Materials in Electronics, 2020, 31, 14466-14477.	2.2	32
35	The possible current-conduction mechanism in the Au/(CoSO ₄ -PVP)/n-Si junctions. Journal of Materials Science: Materials in Electronics, 2020, 31, 18640-18648.	2.2	11
36	On the electrical characteristics of Al/p-Si diodes with and without (PVP: Sn-TeO ₂) interlayer using current-voltage (I-V) measurements. Applied Physics A: Materials Science and Processing, 2020, 126, 1.	2.3	14

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37	Frequency and voltage dependence of electrical and dielectric properties in metal-interfacial layer-semiconductor (MIS) type structures. <i>Physica B: Condensed Matter</i> , 2020, 587, 412122.	2.7	36
38	Intersection behavior of the current-voltage ($I-V$) characteristics of the (Au/Ni)/HfAlO ₃ /n-Si (MIS) structure depends on the lighting intensity. <i>Journal of Materials Science: Materials in Electronics</i> , 2020, 31, 13167-13172.	2.2	9
39	On the frequency and voltage-dependent main electrical parameters of the Au/ZnO/n-GaAs structures at room temperature by using various methods. <i>Physica B: Condensed Matter</i> , 2020, 594, 412274.	2.7	23
40	The origin of anomalous peak and negative capacitance on dielectric behavior in the accumulation region in Au/(0.07 Zn-doped polyvinyl alcohol)/n-4H-SiC metal-polymer-semiconductor structures/diodes studied by temperature-dependent impedance measurements. <i>Journal of Physics and Chemistry of Solids</i> , 2020, 144, 109523.	4.0	26
41	Investigation of the effect of different Bi ₂ O ₃ -x:PVA (x=0, Sm, Sn, Mo) thin insulator interface-layer materials on diode parameters. <i>Journal of Materials Science: Materials in Electronics</i> , 2020, 31, 8033-8042.	2.2	9
42	Frequency-Dependent Admittance Analysis of Au/n-Si Structure with CoSO ₄ -PVP Interfacial Layer. <i>Journal of Electronic Materials</i> , 2020, 49, 3720-3727.	2.2	26
43	Investigation of gamma-irradiation effects on electrical characteristics of Al/(ZnO-xPVA)/p-Si Schottky diodes using capacitance and conductance measurements. <i>Journal of Materials Science: Materials in Electronics</i> , 2020, 31, 8349-8358.	2.2	14
44	The interfacial properties of Au/n-4H-SiC structure with (Zn-doped PVA) interfacial layer. <i>Physica Scripta</i> , 2020, 95, 115809.	2.5	4
45	Investigation of Dielectric Properties, Electric Modulus and Conductivity of the Au/Zn-Doped PVA/n-4H-SiC (MPS) Structure Using Impedance Spectroscopy Method. <i>Zeitschrift Fur Physikalische Chemie</i> , 2020, 234, 505-516.	2.8	5
46	Dielectric properties of Ag/Ru _{0.03} -PVA/n-Si structures. <i>Bulletin of Materials Science</i> , 2019, 42, 1.	1.7	4
47	Dielectric characterization of BSA doped-PANI interlayered metal-semiconductor structures. <i>Journal of Materials Science: Materials in Electronics</i> , 2019, 30, 14224-14232.	2.2	15
48	Determination of current transport and trap states density in AlInGaN/GaN heterostructures. <i>Microelectronics Reliability</i> , 2019, 103, 113517.	1.7	15
49	Investigation of the efficiencies of the (SnO ₂ -PVA) interlayer in Au/n-Si (MS) SDs on electrical characteristics at room temperature by comparison. <i>Journal of Materials Science: Materials in Electronics</i> , 2019, 30, 20479-20488.	2.2	23
50	Examination of dielectric response of Au/HgS-PVA/n-Si (MPS) structure by impedance spectroscopy method. <i>Physica B: Condensed Matter</i> , 2019, 566, 125-135.	2.7	39
51	Synthesis of boron and rare earth stabilized graphene doped polyvinylidene fluoride (PVDF) nanocomposite piezoelectric materials. <i>Polymer Composites</i> , 2019, 40, 3623-3633.	4.6	27
52	On the possible conduction mechanisms in Rhenium/n-GaAs Schottky barrier diodes fabricated by pulsed laser deposition in temperature range of 60-400ÅK. <i>Journal of Materials Science: Materials in Electronics</i> , 2019, 30, 9029-9037.	2.2	21
53	A comparison of electrical parameters of Au/n-Si and Au/(CoSO ₄ -PVP)/n-Si structures (SBDs) to determine the effect of (CoSO ₄ -PVP) organic interlayer at room temperature. <i>Journal of Materials Science: Materials in Electronics</i> , 2019, 30, 9273-9280.	2.2	36
54	The fabrication of Al/p-Si (MS) type photodiode with (%2 ZnO-doped CuO) interfacial layer by sol gel method and their electrical characteristics. <i>Physica B: Condensed Matter</i> , 2019, 560, 91-96.	2.7	39

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55	A comparative study on current/capacitance: voltage characteristics of Au/n-Si (MS) structures with and without PVP interlayer. <i>Journal of Materials Science: Materials in Electronics</i> , 2019, 30, 6491-6499.	2.2	32
56	Determination of Surface States Energy Density Distributions and Relaxation Times for a Metal-Polymer-Semiconductor Structure. <i>IEEE Nanotechnology Magazine</i> , 2019, 18, 1196-1199.	2.0	21
57	Thermal Annealing Effects on the Electrical and Structural Properties of Ni/Pt Schottky Contacts on the Quaternary AlInGaN Epilayer. <i>Journal of Electronic Materials</i> , 2019, 48, 887-897.	2.2	8
58	Frequency-Dependent Admittance Analysis of the Metal-Semiconductor Structure With an Interlayer of Zn-Doped Organic Polymer Nanocomposites. <i>IEEE Transactions on Electron Devices</i> , 2018, 65, 231-236.	3.0	38
59	Effects of a Thin Ru-Doped PVP Interface Layer on Electrical Behavior of Ag/n-Si Structures. <i>Journal of Electronic Materials</i> , 2018, 47, 3510-3520.	2.2	25
60	Preparation and characterization of cross-linked poly (vinyl alcohol)-graphene oxide nanocomposites as an interlayer for Schottky barrier diodes. <i>International Journal of Modern Physics B</i> , 2018, 32, 1750276.	2.0	8
61	Role of Graphene-Doped Organic/Polymer Nanocomposites on the Electronic Properties of Schottky Junction Structures for Photocell Applications. <i>Journal of Electronic Materials</i> , 2018, 47, 7134-7142.	2.2	17
62	Evaluation of Electric and Dielectric Properties of Metal-Semiconductor Structures With 2% GC-Doped-(Ca ₃ Co ₄ Ga _{0.001} O _x) Interlayer. <i>IEEE Transactions on Electron Devices</i> , 2018, 65, 3901-3908.	3.0	30
63	A comparative study on dielectric behaviours of Au/(Zn-doped PVA)/n-4H-SiC (MPS) structures with different interlayer thicknesses using impedance spectroscopy methods. <i>Bulletin of Materials Science</i> , 2018, 41, 1.	1.7	13
64	Preparation of (CuS-PVA) interlayer and the investigation their structural, morphological and optical properties and frequency dependent electrical characteristics of Au/(CuS-PVA)/n-Si (MPS) structures. <i>Journal of Materials Science: Materials in Electronics</i> , 2018, 29, 11801-11811.	2.2	19
65	Dielectric properties, electrical modulus and current transport mechanisms of Au/ZnO/n-Si structures. <i>Progress in Natural Science: Materials International</i> , 2018, 28, 325-331.	4.4	53
66	Effectuality of Barrier Height Inhomogeneity on the Current-Voltage-Temperature Characteristics of Metal Semiconductor Structures with CdZnO Interlayer. <i>Journal of Electronic Materials</i> , 2018, 47, 6059-6066.	2.2	46
67	Temperature and Interfacial Layer Effects on the Electrical and Dielectric Properties of Al/(CdS-PVA)/p-Si (MPS) Structures. <i>Journal of Electronic Materials</i> , 2018, 47, 6600-6606.	2.2	13
68	Preparation of mixed copper/PVA nanocomposites as an interface layer for fabrication of Al/Cu-PVA/p-Si Schottky structures. <i>Physica B: Condensed Matter</i> , 2018, 546, 93-98.	2.7	34
69	Determining electrical and dielectric parameters of Al/ZnS-PVA/p-Si (MPS) structures in wide range of temperature and voltage. <i>Journal of Materials Science: Materials in Electronics</i> , 2018, 29, 12735-12743.	2.2	11
70	Controlling the electrical characteristics of Au/n-Si structure with and without (biphenyl-CoPc) and (OHS ₂ -ZnPc) interfacial layers at room temperature. <i>Polymers for Advanced Technologies</i> , 2017, 28, 952-957.	3.2	6
71	Investigation of photo-induced effect on electrical properties of Au/PPy/n-Si (MPS) type schottky barrier diodes. <i>Journal of Materials Science: Materials in Electronics</i> , 2017, 28, 6413-6420.	2.2	16
72	Investigation of frequency and voltage dependence surface states and series resistance profiles using admittance measurements in Al/p-Si with Co ₃ O ₄ -PVA interlayer structures. <i>Physica B: Condensed Matter</i> , 2017, 515, 28-33.	2.7	43

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73	Two-diode behavior in metal-ferroelectric-semiconductor structures with bismuth titanate interfacial layer. <i>International Journal of Modern Physics B</i> , 2017, 31, 1750197.	2.0	3
74	Electric and Dielectric Properties of Au/ZnS-PVA/n-Si (MPS) Structures in the Frequency Range of 10 ² –200 ⁴ kHz. <i>Journal of Electronic Materials</i> , 2017, 46, 4276-4286.	2.2	34
75	Investigation of the C-V characteristics that provides linearity in a large reverse bias region and the effects of series resistance, surface states and interlayer in Au/n-Si/Ag diodes. <i>Journal of Alloys and Compounds</i> , 2017, 708, 464-469.	5.5	22
76	On the Frequency and Voltage-Dependent Profiles of the Surface States and Series Resistance of Au/ZnO/n-Si Structures in a Wide Range of Frequency and Voltage. <i>Journal of Electronic Materials</i> , 2017, 46, 5728-5736.	2.2	34
77	Determining electrical and dielectric parameters of dependence as function of frequencies in Al/ZnS-PVA/p-Si (MPS) structures. <i>Journal of Materials Science: Materials in Electronics</i> , 2017, 28, 1315-1321.	2.2	38
78	Interfacial layer thickness dependent electrical characteristics of Au/(Zn-doped PVA)/n-Si-4H-SiC (MPS) structures at room temperature. <i>EPJ Applied Physics</i> , 2017, 80, 10101.	0.7	19
79	Frequency and voltage dependence dielectric properties, ac electrical conductivity and electric modulus profiles in Al/Co ₃ O ₄ -PVA/p-Si structures. <i>Physica B: Condensed Matter</i> , 2016, 500, 154-160.	2.7	54
80	Double exponential I–V characteristics and double Gaussian distribution of barrier heights in (Au/Ti)/Al ₂ O ₃ /n-GaAs (MIS)-type Schottky barrier diodes in wide temperature range. <i>Applied Physics A: Materials Science and Processing</i> , 2016, 122, 1.	2.3	57
81	Investigation of Electrical Characteristics in Al/CdS-PVA/p-Si (MPS) Structures Using Impedance Spectroscopy Method. <i>IEEE Transactions on Electron Devices</i> , 2016, 63, 2948-2955.	3.0	79
82	A Comparative Study on the Main Electrical Parameters of Au/Al ₂ O ₃ /n-Si, Au/Biphenyl-CuPc/n-Si and Au/Biphenylsub ₂ -CoPc/n-Si Type Schottky Barrier Diodes. <i>Journal of Nanoelectronics and Optoelectronics</i> , 2016, 11, 620-625.	0.5	5
83	Investigation of dielectric relaxation and ac electrical conductivity using impedance spectroscopy method in (AuZn)/TiO ₂ /p-GaAs(110) schottky barrier diodes. <i>Journal of Alloys and Compounds</i> , 2015, 628, 442-449.	5.5	90
84	The source of negative capacitance and anomalous peak in the forward bias capacitance-voltage in Cr/p-si Schottky barrier diodes (SBDs). <i>Materials Science in Semiconductor Processing</i> , 2015, 39, 484-491.	4.0	74
85	Dielectric properties and electric modulus of Au/PPy/n-Si (MPS) type Schottky barrier diodes (SBDS) as a function of frequency and applied bias voltage. <i>International Journal of Modern Physics B</i> , 2015, 29, 1550075.	2.0	18
86	Dielectric spectroscopy studies and ac electrical conductivity on (AuZn)/TiO ₂ /p-GaAs(110) MIS structures. <i>Philosophical Magazine</i> , 2015, 95, 2885-2898.	1.6	33
87	Comparative study of the temperature-dependent dielectric properties of Au/PPy/n-Si (MPS)-type Schottky barrier diodes. <i>Journal of the Korean Physical Society</i> , 2015, 67, 889-895.	0.7	16
88	Electrical characteristics of Au/PVA (x-doped)/n-Si: Comparison study on the effect of dopant type in PVA. <i>Fibers and Polymers</i> , 2014, 15, 2253-2259.	2.1	2
89	Frequency and voltage-dependent electrical and dielectric properties of Al/Co-doped PVA/p-Si structures at room temperature. <i>Chinese Physics B</i> , 2014, 23, 047304.	1.4	37
90	Single Gaussian distribution of barrier height in Al/PS-ZnPc/p-Si type Schottky barrier diode in temperature range of 120–320 K. <i>Journal of Materials Science: Materials in Electronics</i> , 2014, 25, 4391-4397.	2.2	11

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91	Electrical and dielectric properties and intersection behavior of $G/f^{\%}$ -V plots for Al/Co-PVA/p-Si (MPS) structures at temperatures below room temperature. Journal of the Korean Physical Society, 2014, 65, 2082-2089.	0.7	20
92	Capacitance/Conductanceâ€“Voltageâ€“Frequency Characteristics of $\{m \text{ Au}\}/\{m \text{ PVC}\}+\{m \text{ TCNQ}\}/\{m \text{ p}\}hbox{-}\{m \text{ Si}\}$ Structures in Wide Frequency Range. IEEE Transactions on Electron Devices, 2014, 61, 584-590.	3.0	28
93	Charge transport mechanisms and density of interface traps in MnZnO/p-Si diodes. Journal of Alloys and Compounds, 2014, 590, 157-161.	5.5	69
94	Dielectric and Optical Properties of CdSâ€“Polymer Nanocomposites Prepared by the Successive Ionic Layer Adsorption and Reaction (SILAR) Method. Journal of Electronic Materials, 2014, 43, 1226-1231.	2.2	18
95	Investigation of currentâ€“voltage characteristics and current conduction mechanisms in composites of polyvinyl alcohol and bismuth oxide. Polymer Engineering and Science, 2014, 54, 1811-1816.	3.1	8
96	Frequency and Voltage Dependence of Dielectric Loss of MgB ₂ Composites at Different Temperatures. Journal of Superconductivity and Novel Magnetism, 2013, 26, 2165-2170.	1.8	0
97	A study of polymer-derived erbia-doped Bi ₂ O ₃ nanocrystalline ceramic powders. Journal of Sol-Gel Science and Technology, 2013, 66, 317-323.	2.4	1
98	The origin of negative capacitance in Au/n-GaAs Schottky barrier diodes (SBDs) prepared by photolithography technique in the wide frequency range. Current Applied Physics, 2013, 13, 1101-1108.	2.4	34
99	The effect of metal work function on the barrier height of metal/CdS/SnO ₂ /Inâ€“Ga structures. Current Applied Physics, 2013, 13, 1306-1310.	2.4	15
100	A detailed comparative study on the main electrical parameters of Au/n-Si and Au/PVA:Zn/n-Si Schottky barrier diodes. Materials Science in Semiconductor Processing, 2013, 16, 1865-1872.	4.0	41
101	On the Voltage and Frequency Distribution of Dielectric Properties and ac Electrical Conductivity in Al/SiO ₂ /p-Si (MOS) Capacitors. Chinese Physics Letters, 2013, 30, 017301.	3.3	21
102	The Main Electrical and Interfacial Properties of Benzotriazole and Fluorene Based Organic Devices. Journal of Macromolecular Science - Pure and Applied Chemistry, 2013, 50, 168-174.	2.2	13
103	Analyses of temperature-dependent interface states, series resistances, and AC electrical conductivities of Al/pâ€“Si and Al/Bi ₄ Ti ₃ O ₁₂ /pâ€“Si structures by using the admittance spectroscopy method. Chinese Physics B, 2013, 22, 108502.	1.4	12
104	On the energy distribution of interface states and their relaxation time profiles in Al/pentacene/p-GaAs heterojunction diode. Journal of Applied Physics, 2012, 111, 034508.	2.5	15
105	Effects of interface states and series resistance on electrical properties of Al/nanostructure CdO/p-GaAs diode. Journal of Alloys and Compounds, 2012, 541, 462-467.	5.5	37
106	Temperature dependent negative capacitance behavior of Al/rhodamine-101/n-GaAs Schottky barrier diodes and Rs effects on the Câ€“V and $G/f^{\%}$ -V characteristics. Journal of Alloys and Compounds, 2012, 513, 107-111.	5.5	53
107	The effects of temperature, radiation, and illumination on currentâ€“voltage characteristics of Au/PVA(Co, Znâ€“doped)/nâ€“Si Schottky diodes. Journal of Applied Polymer Science, 2012, 125, 1185-1192.	2.6	18
108	The effect of gamma irradiation on electrical and dielectric properties of Al-TiW-Pd ₂ Si/n-Si Schottky diode at room temperature. Current Applied Physics, 2012, 12, 860-864.	2.4	9

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109	The effect of gamma irradiation on electrical and dielectric properties of organic-based Schottky barrier diodes (SBDs) at room temperature. Radiation Physics and Chemistry, 2012, 81, 362-369.	2.8	25
110	Structural and electrical characterization of rectifying behavior in n-type/intrinsic ZnO-based homojunctions. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2012, 177, 588-593.	3.5	11
111	Illumination intensity effects on the dielectric properties of schottky devices with Co, Ni doped PVA nanofibers as an interfacial layer. Advances in Polymer Technology, 2012, 31, 63-70.	1.7	18
112	The forward bias current density-voltage-temperature ($J-V-T$) characteristics of $Al_2O_3/SiO_2/pSi$ (MIS) Schottky diodes. International Journal of Electronics, 2011, 98, 699-712.	1.4	3
113	The origin of anomalous peak and negative capacitance in the forward bias capacitance-voltage characteristics of Au/PVA/n-Si structures. Journal of Applied Physics, 2011, 109, .	2.5	87
114	On the mechanism of current-transport in Cu/CdS/SnO ₂ /InGa structures. Journal of Alloys and Compounds, 2011, 509, 5555-5561.	5.5	45
115	Analysis of the forward and reverse bias $I-V$ characteristics on Au/PVA:Zn/n-Si Schottky barrier diodes in the wide temperature range. Journal of Applied Physics, 2011, 109, .	2.5	48
116	Illumination Effect on Admittance Measurements of Polyvinyl Alcohol (Co, Zn-Doped) n-Si Schottky Barrier Diodes in Wide Frequency and Applied Bias Voltage Range. , 2011, , .		1
117	Comparative Analysis of Temperature-Dependent Electrical and Dielectric Properties of an $Al/TiW/Pd_2/Si/n-Si$ Schottky Device at Two Frequencies. IEEE Transactions on Electron Devices, 2011, 58, 4042-4048.	3.0	16
118	Electrical characterization of MS and MIS structures on AlGaN/AlN/GaN heterostructures. Microelectronics Reliability, 2011, 51, 370-375.	1.7	43
119	Preparation and dielectric properties of polyvinyl alcohol (Co, Zn Acetate) Fiber/n-Si and polyvinyl alcohol (Ni, Zn Acetate)/n-Si Schottky diodes. Fibers and Polymers, 2011, 12, 886-892.	2.1	11
120	Anomalous Peak in the Forward-Bias $C-V$ Plot and Temperature-Dependent Behavior of Au/PVA (Ni,Zn-doped)/n-Si(111) Structures. Journal of Electronic Materials, 2011, 40, 157-164.	2.2	61
121	The illumination intensity and applied bias voltage on dielectric properties of au/polyvinyl alcohol (Co, Zn doped) n-Si Schottky barrier diodes. Journal of Applied Polymer Science, 2011, 120, 322-328.	2.6	37
122	Temperature dependent current-voltage ($I-V$) characteristics of Au/n-Si (111) Schottky barrier diodes with PVA(Ni,Zn-doped) interfacial layer. Materials Science in Semiconductor Processing, 2011, 14, 139-145.	4.0	57
123	The role of ^{60}Co γ -ray irradiation on the interface states and series resistance in MIS structures. Radiation Physics and Chemistry, 2010, 79, 457-461.	2.8	16
124	The effect of insulator layer thickness on the main electrical parameters in (Ni/Au)/Al _x Ga _{1-x} N/AlN/GaN heterostructures. Surface and Interface Analysis, 2010, 42, 803-806.	1.8	3
125	Illumination effect on electrical characteristics of organic-based Schottky barrier diodes. Journal of Applied Physics, 2010, 108, .	2.5	27
126	Frequency and Temperature Dependence of Dielectric Properties of Au/Polyvinyl Alcohol (Co,) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50 67 T Biomaterials, 2010, 59, 739-756.	3.4	25

#	ARTICLE	IF	CITATIONS
127	The explanation of barrier height inhomogeneities in Au/n-Si Schottky barrier diodes with organic thin interfacial layer. Journal of Applied Physics, 2010, 108, .	2.5	87
128	Temperature dependent negative capacitance behavior in (Ni/Au)/AlGaN/AlN/GaN heterostructures. Journal of Non-Crystalline Solids, 2010, 356, 1006-1011.	3.1	70
129	The distribution of barrier heights in MIS type Schottky diodes from current-voltage-temperature ($I-V-T$) measurements. Journal of Alloys and Compounds, 2009, 479, 893-897.	5.5	67
130	Tunneling current via dislocations in Schottky diodes on AlInN/AlN/GaN heterostructures. Semiconductor Science and Technology, 2009, 24, 075003.	2.0	75
131	Dislocation-governed current-transport mechanism in (Ni/Au)-AlGaN/AlN/GaN heterostructures. Journal of Applied Physics, 2009, 105, .	2.5	89
132	Frequency and gate voltage effects on the dielectric properties of Au/SiO ₂ /n-Si structures. Microelectronic Engineering, 2008, 85, 1910-1914.	2.4	55
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134	The distribution of the barrier height in Al-TiW-Pd ₂ /Si/n-Si Schottky diodes from $I-V$ and $I-T$ measurements. Semiconductor Science and Technology, 2008, 23, 035003.	2.0	20
135	On the profile of frequency and voltage dependent interface states and series resistance in MIS structures. Physica B: Condensed Matter, 2007, 393, 328-335.	2.7	17
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143	All-dielectric Fabry-Perot Cavity Design for Spectrally Selective Mid-Infrared Absorption. Physica Status Solidi (B): Basic Research, 0, , 2100464.	1.5	7